

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

## 2SC6095 — NPN Epitaxial Planar Silicon Transistor High-Voltage Switching Applications

#### **Applicaitons**

• DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter

#### **Features**

- · Adoption of FBET, MBIT process
- · Low collector-to-emitter saturation voltage
- · High allowable power dissipation

- · Large current capacity
- · High-speed switching

#### **Specifications**

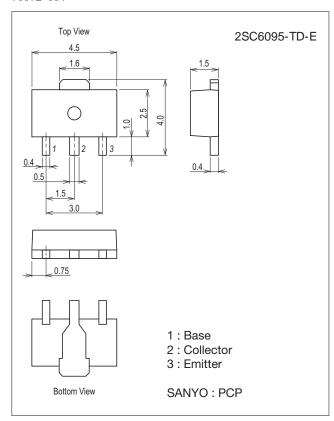
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		120	V
Collector-to-Emitter Voltage	VCES		120	V
	VCEO		80	V
Emitter-to-Base Voltage	VEBO		6.5	V
Collector Current	IC		2.5	А
Collector Current (Pulse)	ICP		4	Α

Continued on next page.

#### **Package Dimensions**

unit : mm (typ) 7007B-004



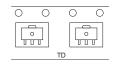
### **Product & Package Information**

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

• Minimum Packing Quantity: 1,000 pcs./reel

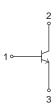
#### Packing Type: TD



## L N

Marking

#### **Electrical Connection**



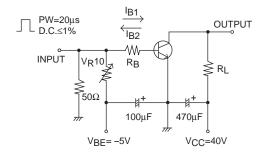
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Parameter	Symbol	Conditions	Ratings	Unit
Base Current	IB		500	mA
Collector Dissipation	Do	When mounted on ceramic substrate (250mm <sup>2</sup> ×0.8mm)	1.3	W
	PC	Tc=25°C	3.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Farameter		Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =70V, I <sub>E</sub> =0A			1	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	300		600	
Gain-Bandwidth Product	fT	VCE=10V, IC=500mA		350		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		14		pF
Collector to Emitter Seturation Valtage	V <sub>CE</sub> (sat)1	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		100	150	mV
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)2	I <sub>C</sub> =1A, I <sub>B</sub> =100mA		90	135	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=1A, IB=100mA		0.9	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0A	120			V
Collector to Emitter Breakdown Valtage	V(BR)CES	I <sub>C</sub> =100μA, R <sub>BE</sub> =0Ω	120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	80			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	6.5			V
Turn-ON Time	ton			40		ns
Storage Time	t <sub>stg</sub>	See specified Test Circuit.		920		ns
Fall Time	tf			32		ns

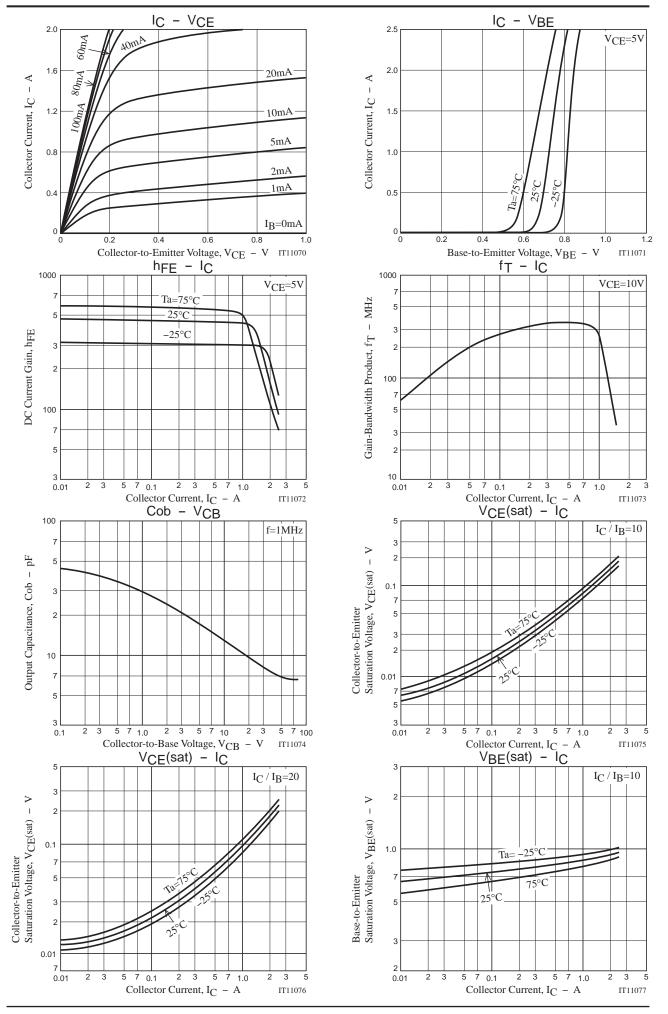
## **Switching Time Test Circuit**

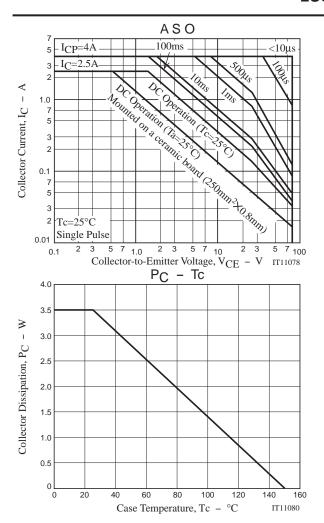


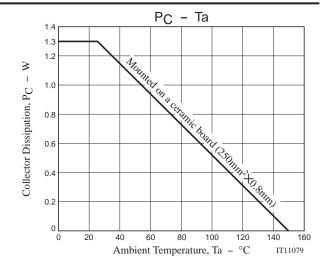
 $IC=10I_{B1}=-10I_{B2}=0.5A$ 

#### **Ordering Information**

Device		Package	Shipping	memo	
	2SC6095-TD-E	PCP	1,000pcs./reel	Pb Free	





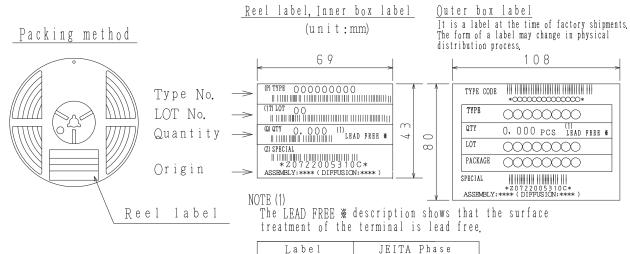


#### **Embossed Taping Specification**

#### 2SC6095-TD-E

#### 1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
PCP	PCP	1, 000	4,000	24,000	4 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



LEAD FREE 3

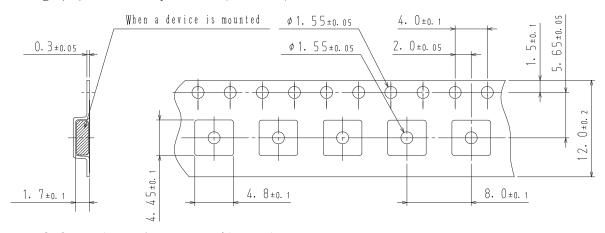
LEAD FREE 4

JEITA Phase 3A

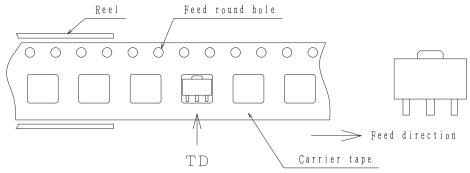
JEITA Phase 3

### 2. Taping configuration

2-1. Carrier tape size (unit:mm)



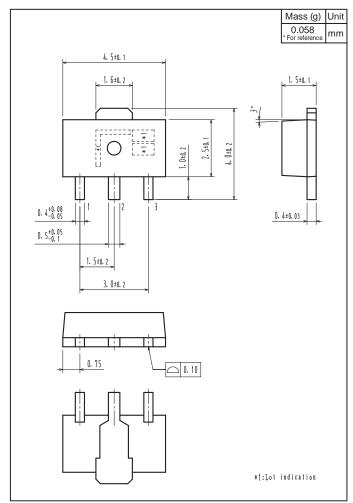
2-2. Device placement direction



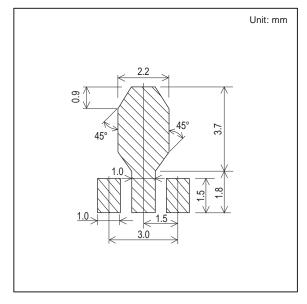
Those with pin 1 index on the feed hole side·····TD

## **Outline Drawing**

2SC6095-TD-E



## **Land Pattern Example**



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